

600 V - 10 A - very fast IGBT

Features

- Low on-voltage drop ($V_{CE(sat)}$)
- Low C_{RES} / C_{IES} ratio (no cross-conduction susceptibility)
- Very soft ultra fast recovery antiparallel diode

Applications

- High frequency motor controls
- SMPS and PFC in both hard switch and resonant topologies
- Motor drivers

Description

This IGBT utilizes the advanced PowerMESH™ process resulting in an excellent trade-off between switching performance and low on-state behavior.

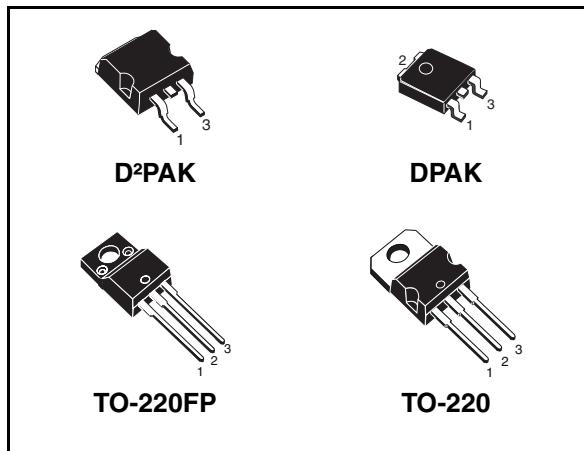


Figure 1. Internal schematic diagram

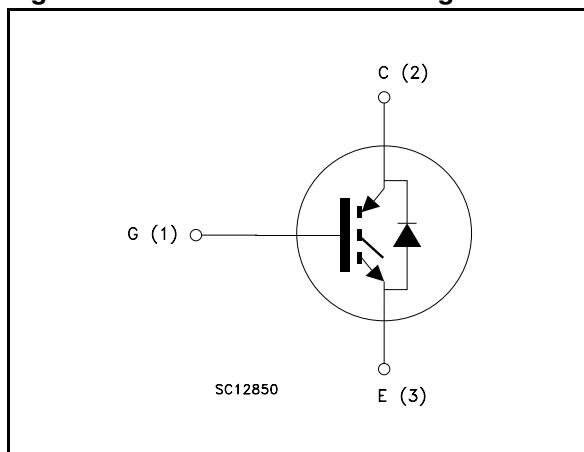


Table 1. Device summary

Order codes	Marking	Package	Packaging
STGB10NC60HDT4	GB10NC60HD	D²PAK	Tape and reel
STGD10NC60HDT4	GD10NC60HD	DPAK	
STGF10NC60HD	GF10NC60HD	TO-220FP	Tube
STGP10NC60HD	GP10NC60HD	TO-220	

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value			Unit
		TO-220 / D ² PAK	DPAK	TO-220FP	
V _{CES}	Collector-emitter voltage ($V_{GE} = 0$)	600			V
I _C ⁽¹⁾	Collector current (continuous) at $T_C = 25^\circ\text{C}$	20	9	9	A
I _C ⁽¹⁾	Collector current (continuous) at $T_C = 100^\circ\text{C}$	10	6	6	A
I _{CL} ⁽²⁾	Turn-off latching current	30			A
I _{CP} ⁽³⁾	Pulsed collector current	30			A
V _{GE}	Gate-emitter voltage	±20			V
I _F	Diode RMS forward current at $T_C = 25^\circ\text{C}$	10			A
I _{FSM}	Surge not repetitive forward current $t_p = 1 \text{ ms sinusoidal}$	20			A
P _{TOT}	Total dissipation at $T_C = 25^\circ\text{C}$	65	62	24	W
V _{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink ($t = 1 \text{ s}; T_C = 25^\circ\text{C}$)	2500			V
T _J	Operating junction temperature	–55 to 150			°C

1. Calculated according to the iterative formula:

$$I_C(T_C) = \frac{T_{j(\max)} - T_C}{R_{thj-c} \times V_{CE(sat)(\max)}(T_{j(\max)}, I_C(T_C))}$$

2. $V_{clamp} = 80\% (V_{CES})$, $V_{GE} = 15 \text{ V}$, $R_G = 10 \Omega$, $T_J = 150^\circ\text{C}$

3. Pulse width limited by max junction temperature allowed

Table 3. Thermal resistance

Symbol	Parameter	Value			Unit
		D ² PAK TO-220	DPAK	TO-220FP	
R _{thj-case}	Thermal resistance junction-case IGBT max.	1.9	2.0	5.1	°C/W
R _{thj-case}	Thermal resistance junction-case diode max.	4	4.5	7	°C/W
R _{thj-amb}	Thermal resistance junction-ambient max.	62.5	100	62.5	°C/W

2 Electrical characteristics

($T_{CASE} = 25^\circ\text{C}$ unless otherwise specified)

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage ($V_{GE} = 0$)	$I_C = 1 \text{ mA}$	600			V
$V_{CE(\text{sat})}$	Collector-emitter saturation voltage	$V_{GE} = 15 \text{ V}, I_C = 5 \text{ A}$ $V_{GE} = 15 \text{ V}, I_C = 5 \text{ A}, T_C = 125^\circ\text{C}$		1.9 1.7	2.5	V
$V_{GE(\text{th})}$	Gate threshold voltage	$V_{CE} = V_{GE}, I_C = 250 \mu\text{A}$	3.75		5.75	V
I_{CES}	Collector cut-off current ($V_{GE} = 0$)	$V_{CE} = 600 \text{ V}$ $V_{CE} = 600 \text{ V}, T_C = 125^\circ\text{C}$			150 1	μA mA
I_{GES}	Gate-emitter leakage current ($V_{CE} = 0$)	$V_{GE} = \pm 20 \text{ V}$			± 100	nA
$g_{fs}^{(1)}$	Forward transconductance	$V_{CE} = 15 \text{ V}, I_C = 5 \text{ A}$		3.5		S

1. Pulse duration = 300 μs , duty cycle 1.5 %

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance			365		pF
C_{oes}	Output capacitance	$V_{CE} = 25 \text{ V}, f = 1 \text{ MHz}$,		43		pF
C_{res}	Reverse transfer capacitance	$V_{GE} = 0$		8.3		pF
Q_g	Total gate charge	$V_{CE} = 390 \text{ V}, I_C = 5 \text{ A}$,		19.2		nC
Q_{ge}	Gate-emitter charge	$V_{GE} = 15 \text{ V}$		4.5		nC
Q_{gc}	Gate-collector charge	(see Figure 19)		7		nC

Table 6. Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r $(di/dt)_{on}$	Turn-on delay time Current rise time Turn-on current slope	$V_{CC} = 390 \text{ V}$, $I_C = 5 \text{ A}$ $R_G = 10 \Omega$, $V_{GE} = 15 \text{ V}$, (see Figure 18) (see Figure 20)		14.2 5 1000		ns ns A/ μs
$t_{d(on)}$ t_r $(di/dt)_{on}$	Turn-on delay time Current rise time Turn-on current slope	$V_{CC} = 390 \text{ V}$, $I_C = 5 \text{ A}$ $R_G = 10 \Omega$, $V_{GE} = 15 \text{ V}$, $T_C = 125^\circ\text{C}$ (see Figure 18) (see Figure 20)		14 5 920		ns ns A/ μs
$t_r(V_{off})$ $t_d(off)$ t_f	Off voltage rise time Turn-off delay time Current fall time	$V_{cc} = 390 \text{ V}$, $I_C = 5 \text{ A}$, $R_{GE} = 10 \Omega$, $V_{GE} = 15 \text{ V}$ (see Figure 18) (see Figure 20)		27 72 85		ns ns ns
$t_r(V_{off})$ $t_d(off)$ t_f	Off voltage rise time Turn-off delay time Current fall time	$V_{cc} = 390 \text{ V}$, $I_C = 5 \text{ A}$, $R_{GE} = 10 \Omega$, $V_{GE} = 15 \text{ V}$, $T_C = 125^\circ\text{C}$ (see Figure 18) (see Figure 20)		50 108 139		ns ns ns

Table 7. Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$E_{on}^{(1)}$ $E_{off}^{(2)}$ E_{ts}	Turn-on switching losses Turn-off switching losses Total switching losses	$V_{CC} = 390 \text{ V}$, $I_C = 5 \text{ A}$ $R_G = 10 \Omega$, $V_{GE} = 15 \text{ V}$, (see Figure 18)		31.8 95 126.8		μJ μJ μJ
$E_{on}^{(1)}$ $E_{off}^{(2)}$ E_{ts}	Turn-on switching losses Turn-off switching losses Total switching losses	$V_{CC} = 390 \text{ V}$, $I_C = 5 \text{ A}$ $R_G = 10 \Omega$, $V_{GE} = 15 \text{ V}$, $T_C = 125^\circ\text{C}$ (see Figure 18)		61.8 173 234.8		μJ μJ μJ

1. E_{on} is the turn-on losses when a typical diode is used in the test circuit in Figure 18. If the IGBT is offered in a package with a co-pak diode, the co-pak diode is used as external diode. IGBTs & Diode are at the same temperature (25°C and 125°C)
2. Turn-off losses include also the tail of the collector current

Table 8. Collector-emitter diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_F	Forward on-voltage	$I_F = 5 \text{ A}$ $I_F = 5 \text{ A}, T_C = 125 \text{ }^\circ\text{C}$		2 1.7	2.45	V V
t_{rr} Q_{rr} I_{rrm}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_F = 5 \text{ A}, V_R = 40 \text{ V},$ $\text{di/dt} = 100 \text{ A}/\mu\text{s}$ <i>(see Figure 21)</i>		22 14 1.3		ns nC A
t_{rr} Q_{rr} I_{rrm}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_F = 5 \text{ A}, V_R = 40 \text{ V},$ $T_C = 125 \text{ }^\circ\text{C}, \text{di/dt} = 100 \text{ A}/\mu\text{s}$ <i>(see Figure 21)</i>		33 30 1.85		ns nC A

2.1 Electrical characteristics (curves)

Figure 2. Output characteristics

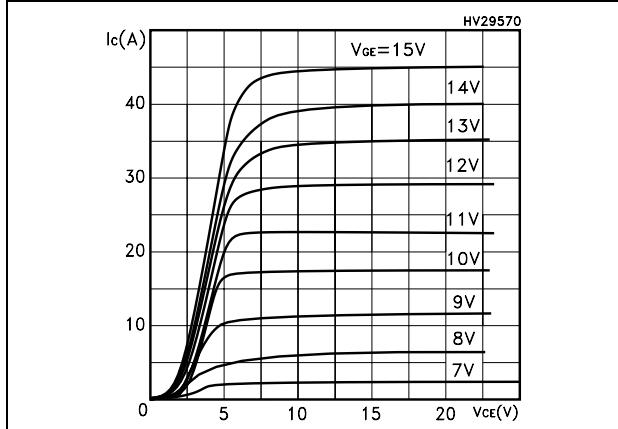


Figure 3. Transfer characteristics

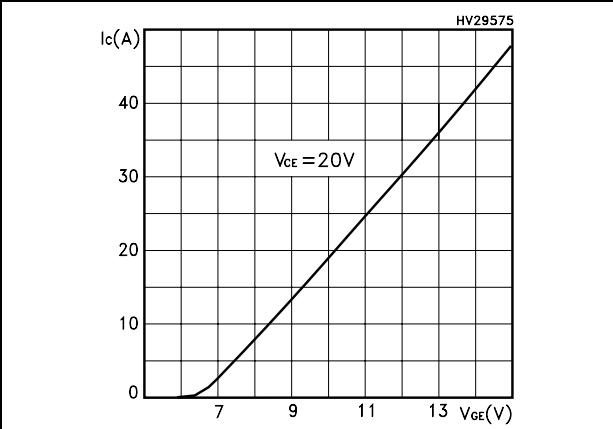


Figure 4. Transconductance

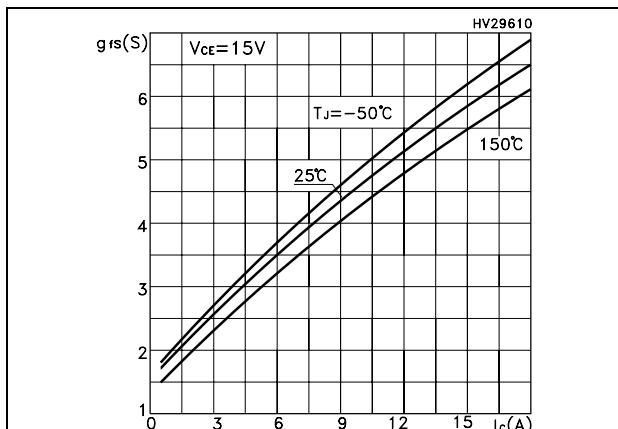


Figure 5. Collector-emitter on voltage vs temperature

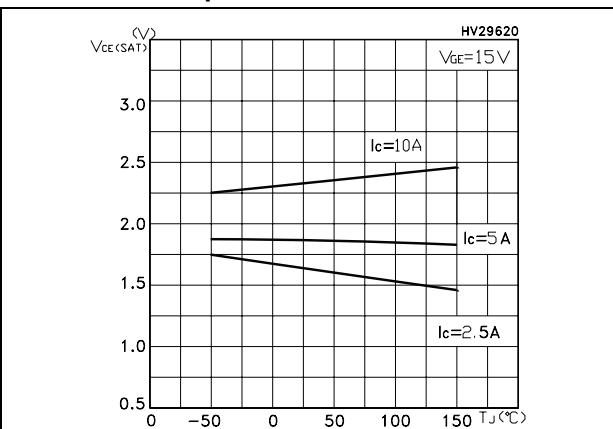


Figure 6. Gate charge vs gate-source voltage

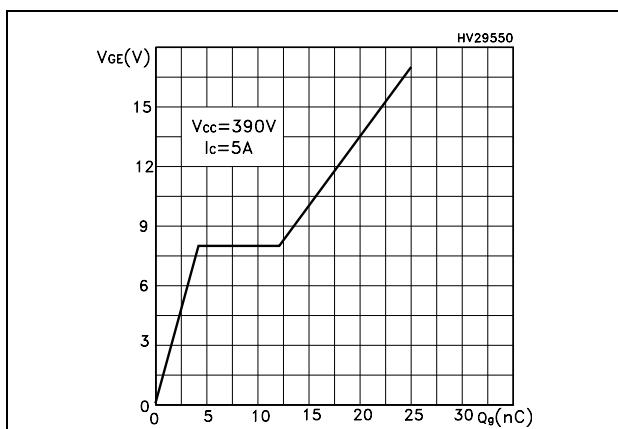


Figure 7. Capacitance variations

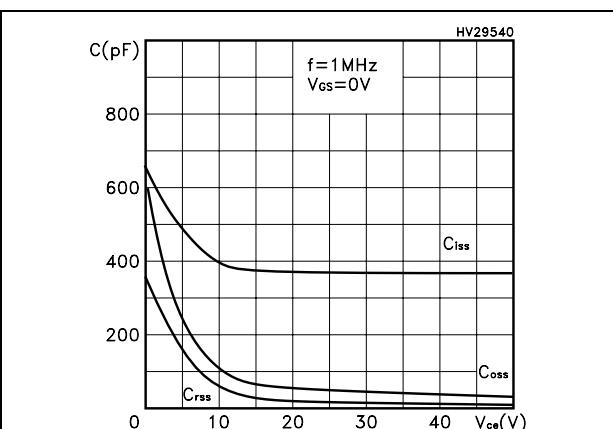


Figure 8. Normalized gate threshold voltage vs temperature

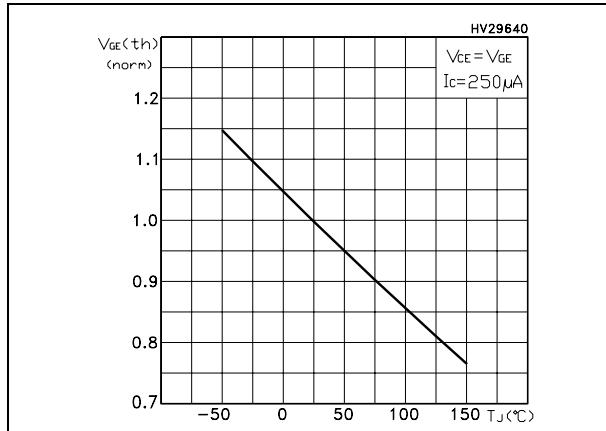


Figure 9. Collector-emitter on voltage vs collector current

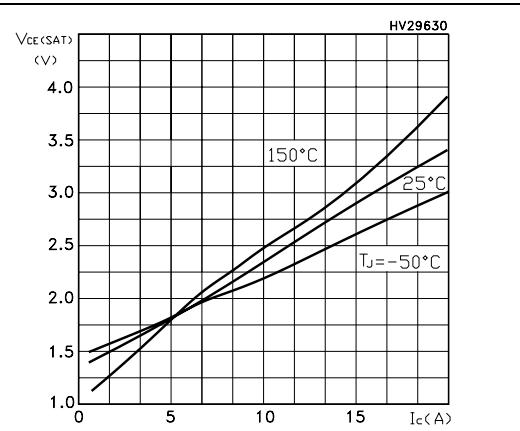


Figure 10. Normalized breakdown voltage vs temperature

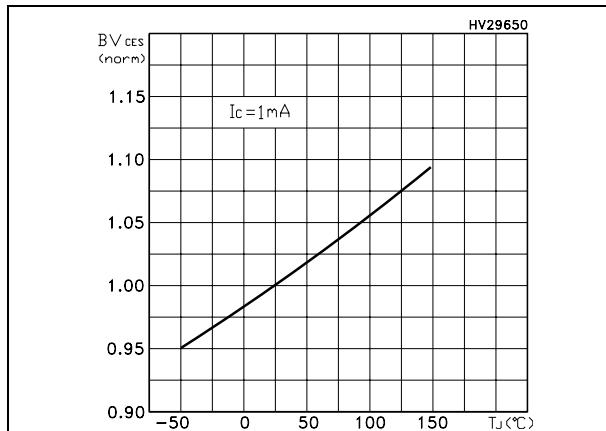


Figure 11. Switching losses vs temperature

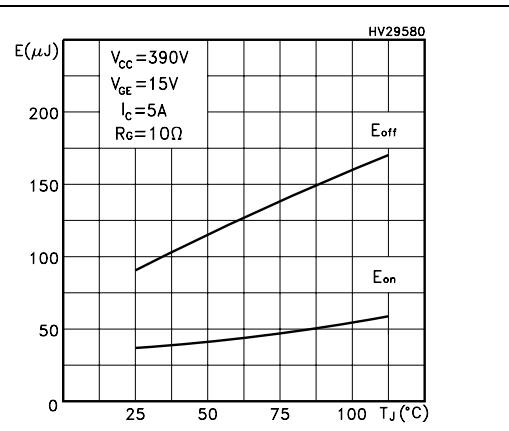


Figure 12. Switching losses vs gate resistance **Figure 13. Switching losses vs collector current**

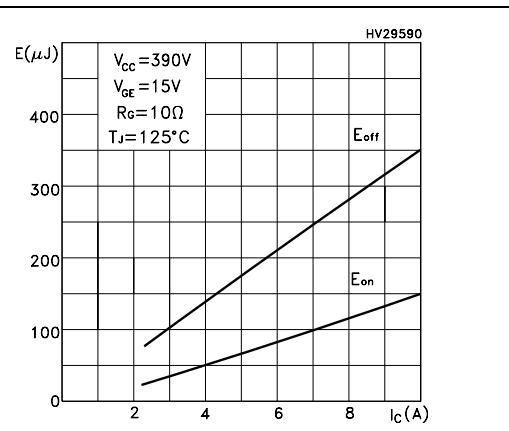
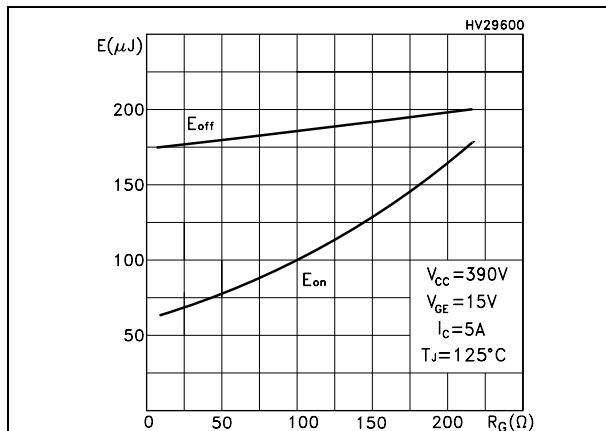


Figure 14. Thermal impedance for TO-220 / D²PAK / DPAK

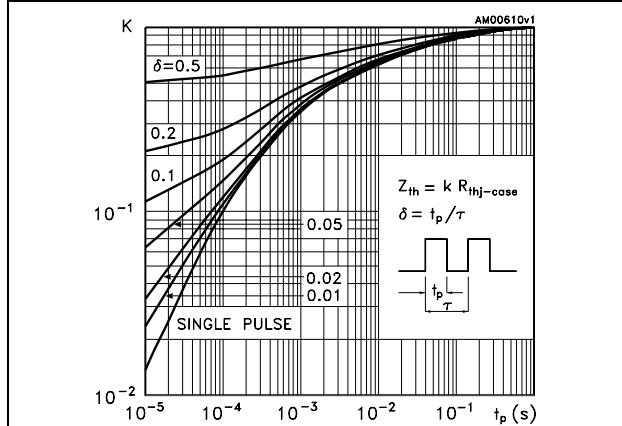


Figure 15. Turn-off SOA

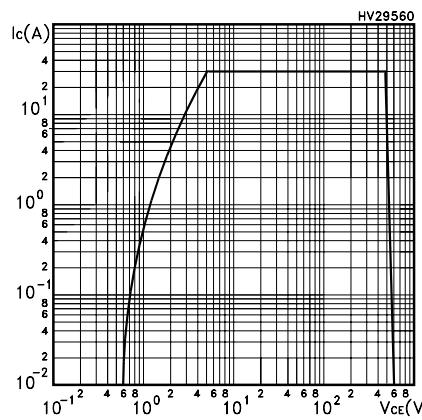
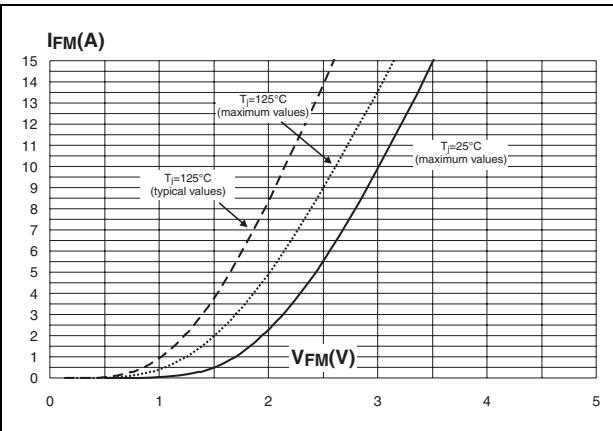
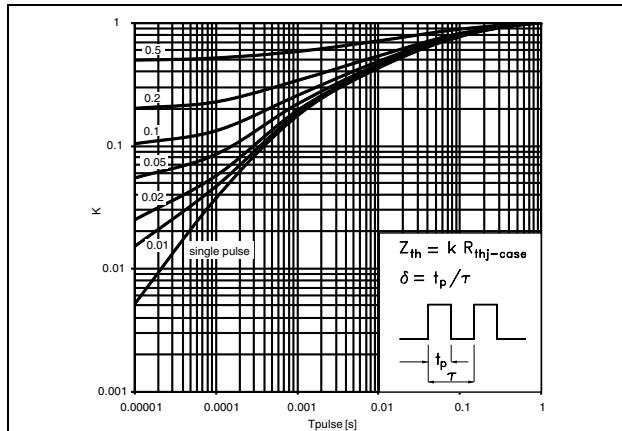


Figure 16. Thermal impedance for TO-220FP

Figure 17. Emitter-collector diode characteristics



3 Test circuit

Figure 18. Test circuit for inductive load switching

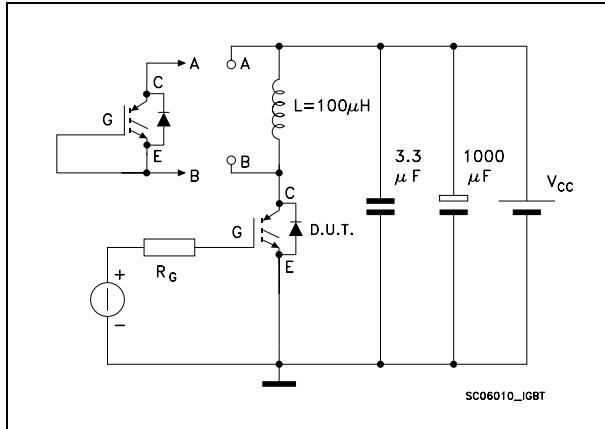


Figure 20. Switching waveform

Figure 19. Gate charge test circuit

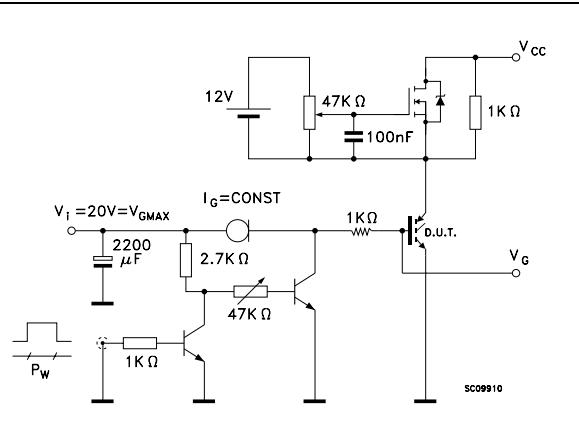
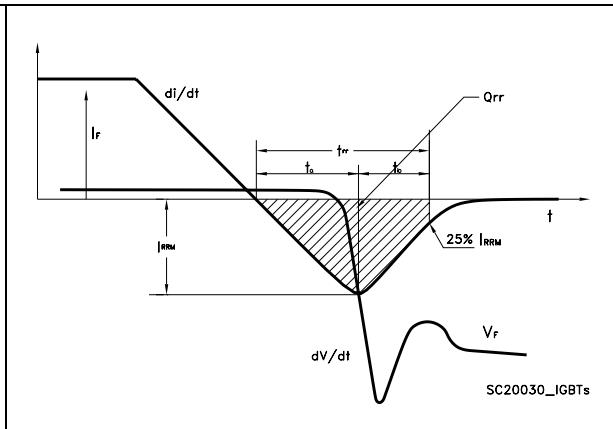
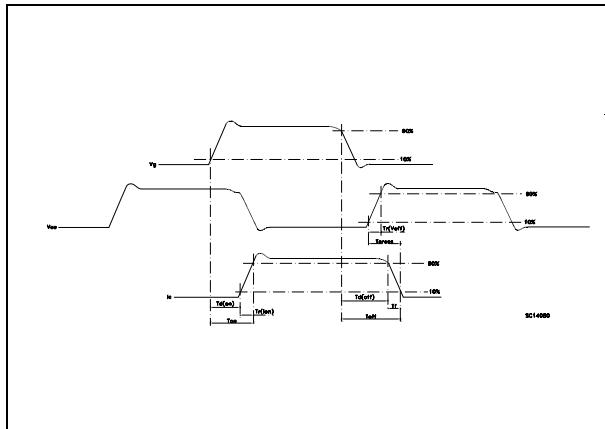


Figure 21. Diode recovery time waveform

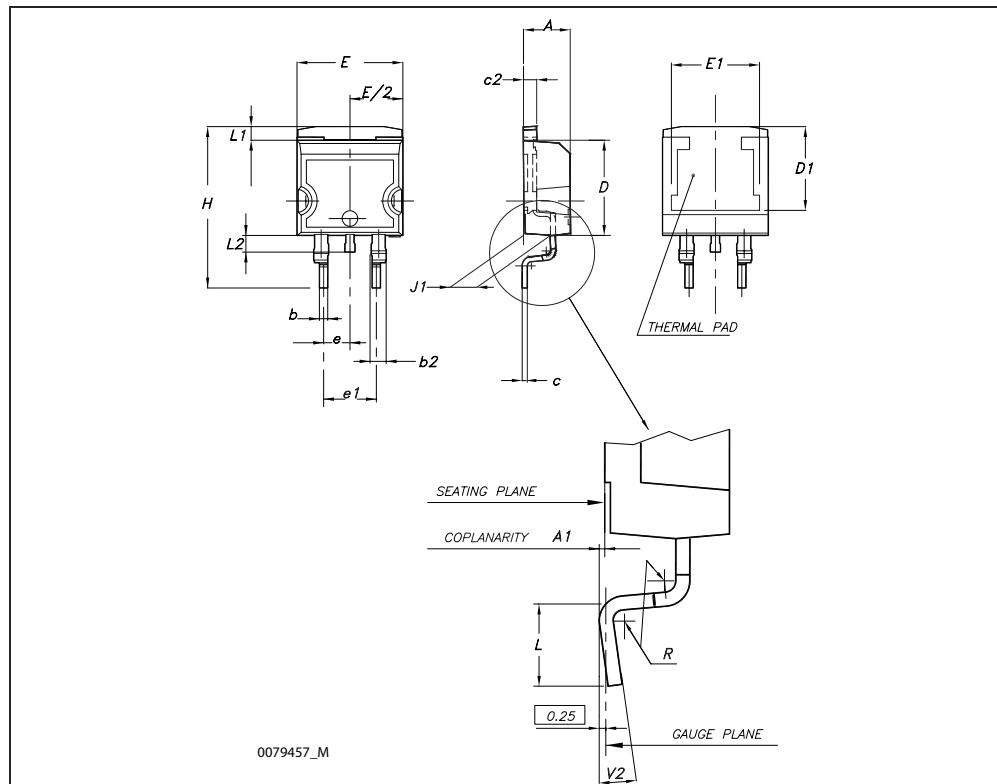


4 Package mechanical data

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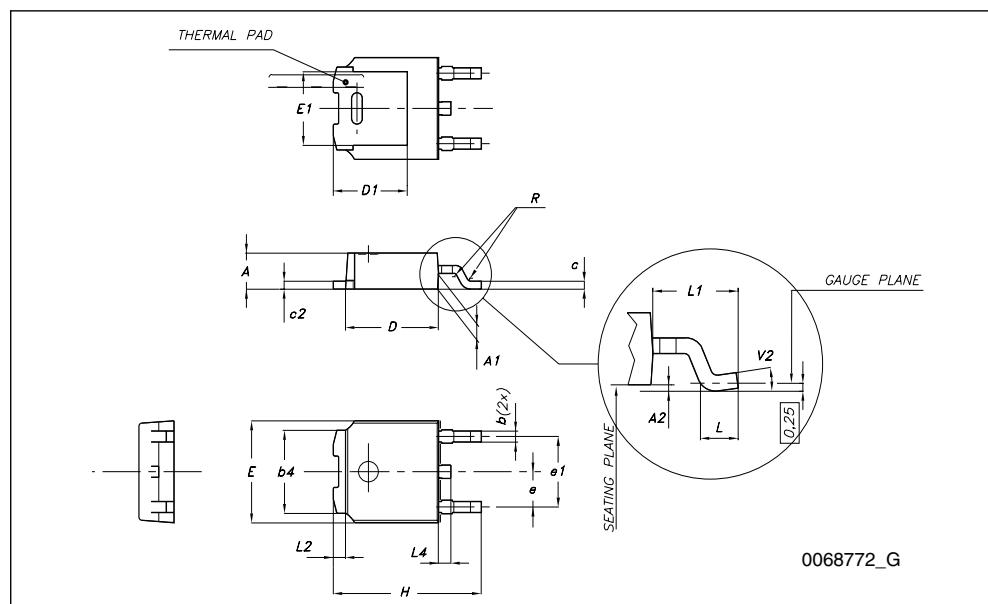
D²PAK (TO-263) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.027		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.017		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50			0.295		
E	10		10.40	0.394		0.409
E1	8.50			0.334		
e		2.54			0.1	
e1	4.88		5.28	0.192		0.208
H	15		15.85	0.590		0.624
J1	2.49		2.69	0.099		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.05		0.055
L2	1.30		1.75	0.051		0.069
R		0.4			0.016	
V2	0°		8°	0°		8°



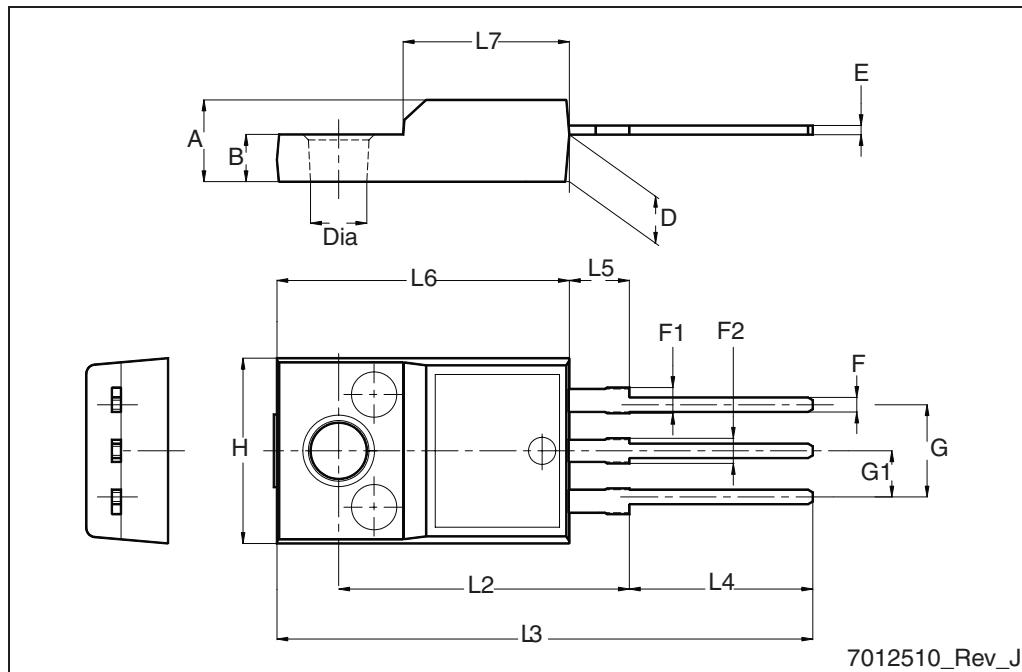
TO-252 (DPAK) mechanical data

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0 °		8 °



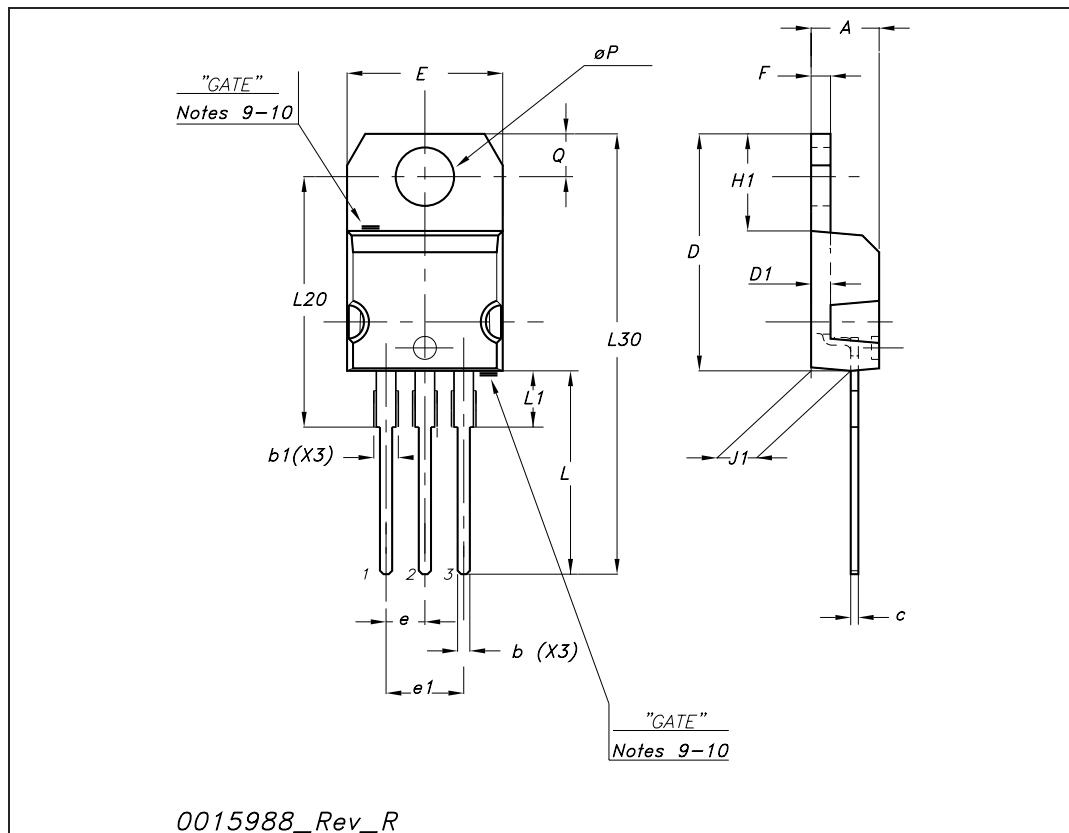
TO-220FP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.5
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2



TO-220 mechanical data

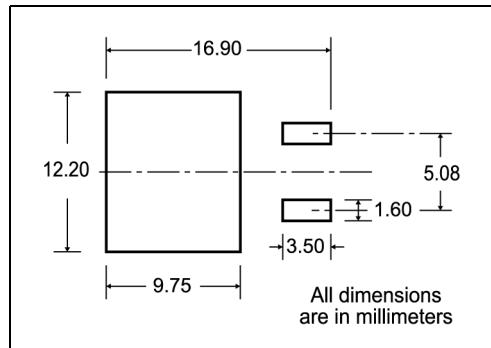
Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.48		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
$\emptyset P$	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



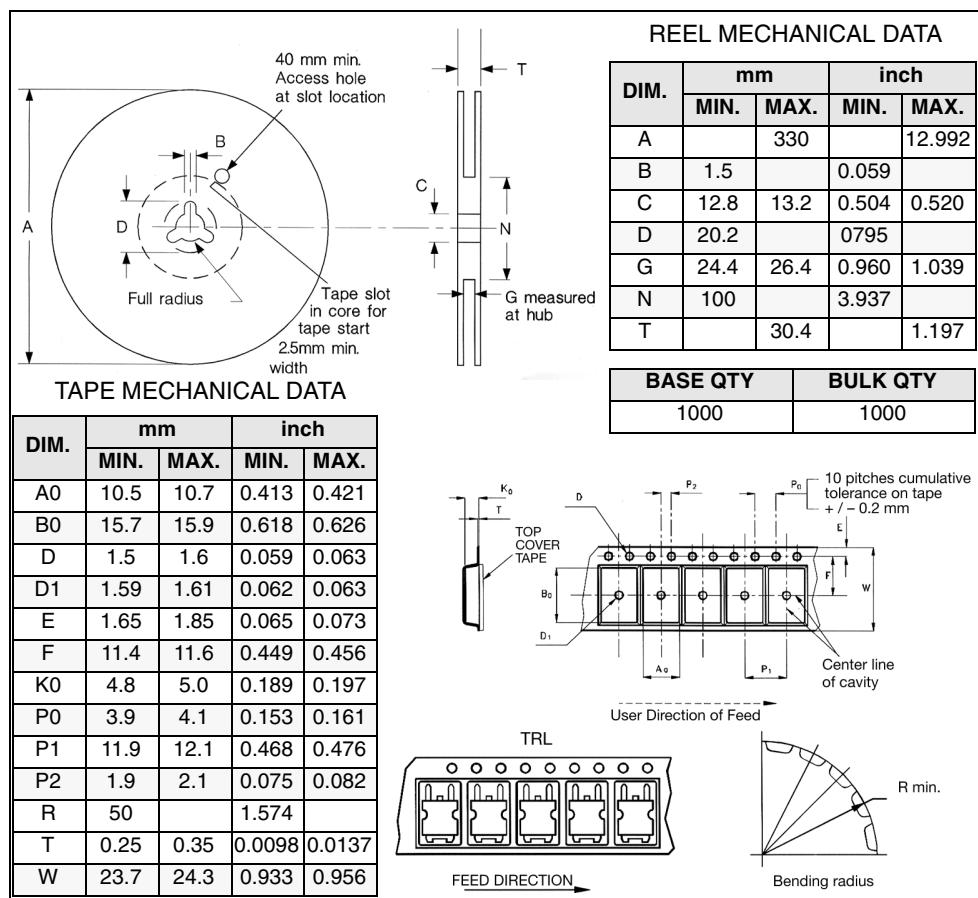
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4.1 Packaging mechanical data

D²PAK FOOTPRINT

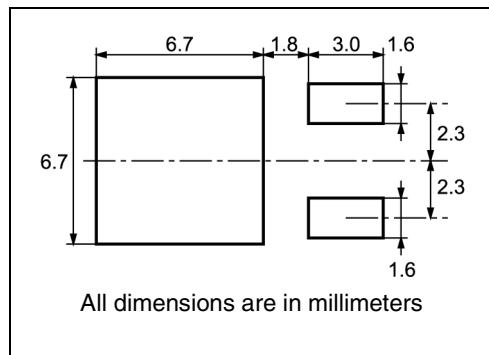


TAPE AND REEL SHIPMENT

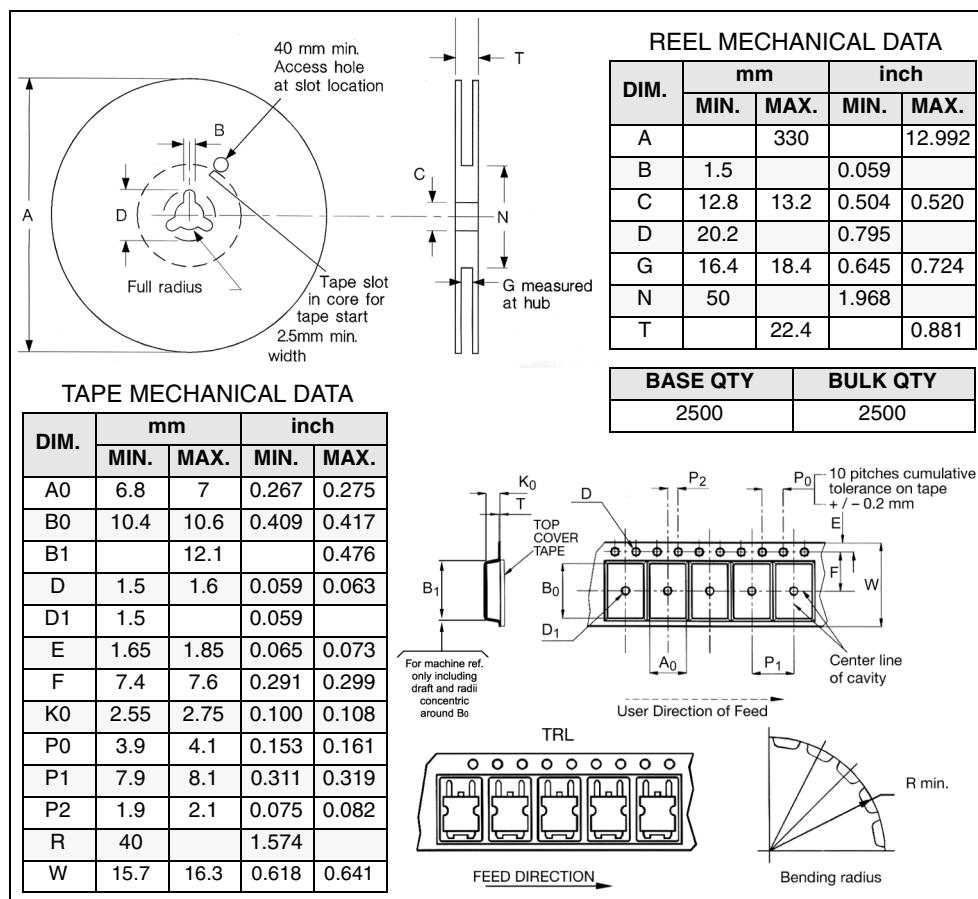


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DPAK FOOTPRINT



TAPE AND REEL SHIPMENT



5 Revision history

Table 9. Document revision history

Date	Revision	Changes
30-Jan-2006	1	Initial release
06-Nov-2006	2	Complete version
08-Feb-2007	3	The document has been reformatted
05-Oct-2007	4	Added TO-220FP, Table 2 has been updated
16-Dec-2008	5	Added DPAK package

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